

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	3477	(silicon wafer layer stack) with magnet\$7 with anneal\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/20 11:18
S2	58	S1 and ((magnet\$7 near\$5 anneal\$5) with wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 08:10
S3	4	S2 and (anneal\$5 with (lamp laser flashlight rta))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 07:25
S4	268	(magnetoresist\$5 wafer) with magnet\$7 with anneal\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 07:24
S5	11	S4 and (anneal\$5 with (lamp laser flashlight rta))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 07:57
S6	1	("6649423").PN.	USPAT; USOCR	OR	OFF	2005/08/28 07:57

S7	0	S4 and ("spot to spot" "line to line")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 08:11
S8	0	S1 and ("spot to spot" "line to line")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 08:11
S9	0	("spot to spot" "line to line")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 08:11
S10	0	"spot to spot"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 08:11
S11	11061	spot near2 spot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 08:12
S12	303338	line near2 line	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 08:12
S13	313209	S11 S12	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 08:12

S14	209	S13 with anneal\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 08:24
S15	3	S13 with anneal\$5 with wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 08:13
S16	209	S14	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 08:37
S17	7	(S13 with anneal\$5) and (anneal\$5 with wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 08:25
S18	1987	wafer with (cooled cooling cool) with (helium argon nitrogen vacuum)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 08:38
S19	16	wafer with (cooled cooling cool) with (helium argon nitrogen vacuum) with (anneal\$ near\$5 temperature)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 09:28
S20	4441	219/121.6,121.65,121.66,121.84,121.85.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 09:28

S21	1	S20 and (wafer with anneal\$5 with magnet\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 09:29
S22	1	S20 and (wafer with anneal\$5) and (wafer with magnet\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 09:29
S23	7	S20 and ((silicon layer stack wafer) with anneal\$5) and ((silicon layer stack wafer) with magnet\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/28 09:30
S24	186741	"438"/\$.cds.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 12:08
S25	2	S24 and (wafer with magnet\$4 with field with anneal\$4). clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 12:15
S26	12	S24 and (wafer with magnet\$4 with field with anneal\$4) not S25	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 12:15
S27	12	S24 and (wafer with magnet\$4 near3 field with anneal\$4) not S25	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 12:27

S28	5	S26 and (anneal\$5 near\$5 (entir\$5 local\$4 part portion))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 12:33
S29	4	S26 and (anneal\$5 near\$5 (entir\$5 local\$4 part portion) and degree)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 13:02
S30	5	S26 and (anneal\$5 near\$5 (entir\$5 local\$4 part portion) and (anneal\$5 with (temp temperature "C")))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 12:57
S31	1	("6918965").PN.	USPAT; USOCR	OR	OFF	2006/09/20 12:43
S32	1	("4390392").PN.	USPAT; USOCR	OR	OFF	2006/09/20 12:43
S33	2	S31 S32	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 12:44
S34	1	S33 and magnetic\$5 with anneal\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 12:44
S35	3	S26 and magnetic\$5 with stack	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 12:57

S36	3	S26 and (anneal\$5 near5 (select\$9 local\$4 part portion))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 13:07
S37	2	S26 and (anneal\$5 near5 (select\$9 local\$4 part portion)) and ((lamp laser light rta flashlight) with anneal\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 13:09
S38	1	S26 and (anneal\$5 near5 (select\$9 local\$4 part portion)) and ((pin pinned pinning) with (magnetic\$4 layer\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 13:10
S39	8	S26 and ((pin pinned pinning) with (magnetic\$4 layer\$4)) not S38	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 13:15
S40	2	S26 and (cool\$4 same (liquid helium nitrogen argon vacuum))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 13:16
S41	25	(magnetic near5 stack) same (cool\$4 same (liquid helium nitrogen argon vacuum))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 13:16
S42	20	(magnetic near5 stack) same (cool\$4 with (liquid helium nitrogen argon vacuum))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 13:17

S43	0	(wafer with anneal\$4) and (magnetic near5 stack) same (cool\$4 with (liquid helium nitrogen argon vacuum))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 13:18
S44	309	(wafer with anneal\$4) and (wafer with (cool\$4 with (liquid helium nitrogen argon vacuum)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 13:18
S45	111	(wafer with anneal\$4) and (anneal\$4 same wafer with (cool\$4 with (liquid helium nitrogen argon vacuum)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 13:19
S46	3	(wafer with anneal\$4) and ((anneal\$4 with (portion point)) same wafer with (cool\$4 with (liquid helium nitrogen argon vacuum)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 13:21
S47	3	(wafer with anneal\$4) and ((anneal\$4 with (section part portion point)) same wafer with (cool\$4 with (liquid helium nitrogen argon vacuum))) not S46	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 13:24
S48	3	((anneal\$4 with (section part portion point)) same wafer with (cool\$4 with (liquid helium nitrogen argon vacuum))) not S46	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 13:24
S49	49	((anneal\$4 with wafer) with (cool\$4 near5 (liquid helium nitrogen argon vacuum))) not S47 not S48	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 13:25

S50	6197655	b0\$9 b1\$9 b2\$9 b3\$9 b4\$9 b5\$9 b6\$9 b7\$9 b8\$9 b9\$9 f0\$9 f1\$9 f2\$9 f3\$9 f4\$9 f5\$9 f6\$9 f7\$9 f8\$9 f9\$9 g0\$9 g1\$9 g2\$9 g3\$9 g4\$9 g5\$9 g6\$9 g7\$9 g8\$9 g9\$9 h0\$9 h1\$9 h2\$9 h3\$9 h4\$9 h5\$9 h6\$9 h7\$9 h8\$9 h9\$9	JPO	OR	ON	2007/02/26 13:16
S51	989	S50 and (anneal\$4 and (wafer silicon) and magnet\$7)	JPO	OR	ON	2007/02/26 13:17
S52	10	S50 and (anneal\$4 and (wafer silicon) and magnet\$7 with field and magnet\$7 with (layer portion part area))	JPO	OR	ON	2007/02/26 13:26
S53	0	(anneal\$4 and wafer and magnet\$7 with field and magnet\$7 with (layer portion part area)) not S52	JPO	OR	ON	2007/02/27 12:07
S54	6197655	b0\$9 b1\$9 b2\$9 b3\$9 b4\$9 b5\$9 b6\$9 b7\$9 b8\$9 b9\$9 f0\$9 f1\$9 f2\$9 f3\$9 f4\$9 f5\$9 f6\$9 f7\$9 f8\$9 f9\$9 g0\$9 g1\$9 g2\$9 g3\$9 g4\$9 g5\$9 g6\$9 g7\$9 g8\$9 g9\$9 h0\$9 h1\$9 h2\$9 h3\$9 h4\$9 h5\$9 h6\$9 h7\$9 h8\$9 h9\$9	JPO	OR	ON	2007/02/27 12:07
S55	10	S54 and (anneal\$4 and (wafer silicon) and magnet\$7 with field and magnet\$7 with (layer portion part area))	JPO	OR	ON	2007/02/27 12:07
S56	30	(anneal\$4 and wafer and (magnet\$7 field) with (layer portion part area)) not S55	JPO	OR	ON	2007/02/27 12:09
S57	10	(anneal\$4 and wafer and magnet\$7 and (magnet\$7 field) with (layer portion part area))	JPO	OR	ON	2007/02/27 12:12
S58	6	S54 and (anneal\$4 and wafer with field with (layer portion part area))	JPO	OR	ON	2007/02/27 12:13
S59	0	S54 and (anneal\$4 and wafer with magnet\$7 with field with (layer portion part area))	JPO	OR	ON	2007/02/27 12:13
S60	0	(anneal\$4 and wafer with magnet\$7 with field with (layer portion part area))	JPO	OR	ON	2007/02/27 12:14
S61	152	(anneal\$4 and wafer with magnet\$7 with field with (layer portion part area))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 12:14

S62	46	((anneal\$4 same wafer with magnet\$7 with field with (layer portion part area))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 12:14
S63	34	((anneal\$4 with magnet\$7 with wafer) same (wafer with magnet\$7 with field with (layer portion part area)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 12:15
S64	9	((anneal\$4 with magnet\$7 with wafer) same ((magnet\$7 field) near5 (layer portion part area) near (wafer silicon)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 12:17
S65	23	wafer with (magnetic adj field) with (magnetic adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 12:18
S66	8	wafer with ((apply\$9 application) near3 magnet\$4) with (magnetic adj field) with (magnetic adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 12:58
S67	1	wafer with ((apply\$9 application) near3 magnet\$4) with (magnetic adj field) same (magnetic near3 layer) same (((local\$9 part\$5 section\$4) near4 layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 13:14
S68	320	wafer near5 region near5 anneal\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 13:31

S69	62	wafer near2 region near2 anneal\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 13:16
S70	28	anneal\$4 near2 region adj2 wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 13:16
S71	0	wafer near5 region near5 anneal\$4 with pin\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 13:31
S72	0	wafer near5 region near5 anneal\$4 and (magnet\$4 with pin\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 13:32
S73	0	wafer near5 region near5 anneal\$4 and pinning	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 13:32
S74	37	wafer with anneal\$4 same pinning	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 13:36
S75	7	wafer with anneal\$4 same pinning and magnet\$9 with vector	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 13:45

S76	11	(wafer with anneal\$4 same pinning) and (chang\$4 with direction with field)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 13:48
S77	15	(wafer with anneal\$4 with pin\$4) and (chang\$4 with direction with (magnet\$7 field))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 13:51
S78	3	(wafer with anneal\$4 with pin\$4) and (align\$4 near\$5 pin\$5) and (chang\$4 with direction with (magnet\$7 field))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/28 08:29
S79	597	(wafer with anneal\$4 with degrees)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/28 09:21
S80	118	(wafer with anneal\$4 with degrees with ("300" "500"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/28 08:30
S81	4	(wafer with anneal\$4 with degrees with ("300" "500") same (pin\$4 magnetic\$5))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/09 13:21
S82	45	(wafer with anneal\$4 with degrees with ("300" "500") with second)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/28 08:34

S83	0	(wafer with anneal\$4 with degrees with ("300" "500") with second) and (magnet\$5 with pin\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/28 08:34
S84	0	(wafer with anneal\$4 with degrees with ("300" "500") with second) same magnet\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/28 08:36
S85	0	wafer and anneal\$4 and degrees and ("300" "500") and (second sec "s") and magnet\$5	JPO	OR	ON	2007/02/28 08:37
S86	0	wafer and anneal\$4 and ("300" "500") and (second sec "s") and magnet\$5	JPO	OR	ON	2007/02/28 08:37
S87	5	wafer and anneal\$4 and ("300" "500") and (second sec "s")	JPO	OR	ON	2007/02/28 08:39
S88	137	(wafer silicon) and (anneal\$4 treat\$4) and ("300" "500") and (second sec "s")	JPO	OR	ON	2007/02/28 08:41
S89	87	(wafer silicon) and (anneal\$4 treat\$4) and ("300" "500") and (second sec "s") not steel	JPO	OR	ON	2007/02/28 08:42
S90	26	wafer and (anneal\$4 treat\$4) and ("300" "500") and (second sec "s") not steel	JPO	OR	ON	2007/02/28 09:06
S91	16	wafer and anneal\$4 and (cool\$4 with (liquid helium nitrogen argon vacuum))	JPO	OR	ON	2007/02/28 09:16
S92	1	wafer and anneal\$4 and (cool\$4 near\$5 portion)	JPO	OR	ON	2007/02/28 10:54
S93	10	wafer and anneal\$4 and (cool\$4 with (portion section part))	JPO	OR	ON	2007/02/28 09:20
S94	0	wafer and anneal\$4 and (cool\$4 near\$2 select\$7)	JPO	OR	ON	2007/02/28 09:21
S95	0	wafer and anneal\$4 and (cool\$4 near\$2 portion)	JPO	OR	ON	2007/02/28 09:21

S96	0	(wafer with anneal\$4 with selectively near2 cool\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/28 09:22
S97	0	(wafer with anneal\$4 same selectively near2 cool\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/28 09:22
S98	25	(wafer with anneal\$4 and selectively near2 cool\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/28 09:22
S99	10	(wafer with anneal\$4 and wafer with selectively near2 cool\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/28 09:24
S100	0	(wafer with selectively near2 cool\$4)	JPO	OR	ON	2007/02/28 09:25
S101	2	(wafer and selectively near2 cool\$4)	JPO	OR	ON	2007/02/28 09:25
S102	1	("6294911").PN.	USPAT; USOCR	OR	OFF	2007/02/28 10:54
S103	1	("6294911").PN.	USPAT; USOCR	OR	OFF	2007/08/09 13:24
S104	90	wafer with anneal\$4 with magnetic\$3 adj field	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/09 13:53

S105	26	S104 same magnetic near2 layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/09 13:26
S106	8	(wafer with anneal\$4 with magnetic\$3 adj field).dm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/09 13:59
S107	70	(magnetic adj stack).dm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/09 14:00
S108	5	S107 and thermal\$5 near3 magnet\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/09 14:05
S109	1	S107 and thermal\$5 near3 treat\$5 with magnet\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/09 14:06
S110	3	S107 and anneal\$4 with magnet\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/09 14:06
S111	1	S107 and heat\$3 near5 magnet\$4 not S109 not S110	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/09 14:08

S112	386	wafer same heat\$3 near5 magnet\$4 not S109 not S110	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/09 14:08
S113	191	wafer with heat\$3 near5 magnet\$4 not S109 not S110	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/09 14:09
S114	40	S113 and anneal\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/09 14:09
S115	34	S113 and anneal\$4 near5 (magnet\$5 layer wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 10:34
S116	34	S115 and field	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/09 14:13
S117	31	S115 and magnet\$4 near3 field	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/09 14:13
S118	28	S115 and magnet\$4 near3 field same anneal\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/09 14:21

S119	4	S118 and align\$4 near3 pin\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/09 14:28
S120	11	S118 and (align\$4 field) near3 pin\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/09 14:28
S121	70	(magnetic adj stack).dm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 10:34
S122	1	S121 and thermal\$5 near3 treat\$5 with magnet\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 10:34
S123	3	S121 and anneal\$4 with magnet\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 10:34
S124	191	wafer with heat\$3 near5 magnet\$4 not S122 not S123	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 10:45
S125	34	S124 and anneal\$4 near5 (magnet\$5 layer wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 10:34

S126	29	S125 and "C"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 12:59
S127	16	S125 and heat adj treat\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 10:37
S128	10	S125 and (pinn\$3 pin magent\$4 anneal\$4) near5 ("c" "C")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 10:39
S129	1	S125 and (pinn\$3 pin magent\$4 anneal\$4) near5 ("c" "C") with (second minute min)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 10:40
S130	18	S125 and ("c" "C") with (second minute min) not S129	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 10:41
S131	4	S125 and ("c" "C") with second not S129	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 10:43
S132	1	S124 and (heat treat\$4) with ("c" "C") with second not S129 not S131	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 10:43

S133	0	S124 and (heat treat\$4) with ("c" "C") with sec not S129 not S131	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 10:44
S134	0	S124 and (heat treat\$4) with ("c" "C") with "s" not S129 not S131	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 10:44
S135	50	wafer same heat\$3 with magnet\$4 with seconds	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 10:45
S136	33	wafer same heat\$3 with magnet\$4 with field with seconds	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 10:46
S137	25	S136 and (pinn\$3 pin) with (magnetic\$4 heat treat\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 10:47
S138	33	wafer same heat\$3 with magnet\$4 with field with "seconds"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 12:33
S139	25	S138 and (pinn\$3 pin) with (magnetic\$4 heat treat\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 10:52

S140	5	S138 and (pinn\$3 pin) with (magnetic\$4 heat treat\$4) with time	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 10:52
S141	76	wafer same (heat\$3 treat\$4 anneal\$4 pinn\$4) with magnet\$4 with field with ("seconds" minute)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 10:57
S142	2	wafer same (heat\$3 treat\$4 anneal\$4 pinn\$4) with magnet\$4 with field with ("seconds" minute) not "second"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 10:56
S143	84	wafer same (heat\$3 treat\$4 anneal\$4 pinn\$4) with magnet\$4 with field with ("seconds" sec min minute)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 10:57
S144	84	wafer same (heat\$3 treat\$4 anneal\$4 pinn\$4) with magnet\$4 with field with (seconds sec min minute)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 10:57
S145	4	wafer same (heat\$3 treat\$4 anneal\$4 pinn\$4) with magnet\$4 with field with time with (seconds sec min minute)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 10:58
S146	6	wafer same (heat\$3 treat\$4 anneal\$4 pinn\$4) with magnet\$4 with field with (time period) with (seconds sec min minute)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 11:00

S147	0	wafer same (heat\$3 treat\$4 anneal\$4 pinn\$4) with magnet\$4 with field with (time period) with less adj than with minute	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 11:02
S148	0	wafer same (heat\$3 treat\$4 anneal\$4 pinn\$4) with magnet\$4 with field with less adj than with minute	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 11:00
S149	0	(heat\$3 treat\$4 anneal\$4 pinn\$4) with magnet\$4 with field with less adj than with minute	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 11:01
S150	0	(heat\$3 treat\$4 anneal\$4 pinn\$4) with less adj than with minute same wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 11:01
S151	0	(heat\$3 treat\$4 anneal\$4 pinn\$4) with less adj than with (minute second)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 11:01
S152	0	(heat\$3 treat\$4 anneal\$4 pinn\$4) with less adj than	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 11:01
S153	9	less adj than	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 11:02

S154	0	wafer same (heat\$3 treat\$4 anneal\$4 pinn\$4) with magnet\$4 with field with (time period) with less with minute	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 11:03
S155	67	wafer same (heat\$3 treat\$4 anneal\$4 pinn\$4) with (time period) with less with minute	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 11:03
S156	36	wafer same (heat\$3 treat\$4 anneal\$4 pinn\$4) with (time period) with less adj4 minute	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 11:04
S157	3	wafer same (heat\$3 treat\$4 anneal\$4 pinn\$4) with (time period) with less adj4 minute and pin\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 11:05
S158	49	wafer and (heat\$3 treat\$4 anneal\$4 pinn\$4) with (time period) with less adj4 minute and pin\$4 not S157	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 11:08
S159	0	wafer same pinn\$4 and (heat\$3 treat\$4 anneal\$4) with (time period) with less adj4 minute and pin\$4 not S157	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 11:06
S160	1	wafer with anneal\$4 and (heat\$3 treat\$4 anneal\$4 pinn\$4) with (time period) with less adj4 minute and pin\$4 not S157	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 11:08

S161	43	wafer with (heat\$3 treat\$4 anneal\$4 pinn\$4) same (time period) with less adj 4 (minute second sec) and pin\$4 not S157	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 11:12
S162	88	wafer with (heat\$3 treat\$4 anneal\$4 pinn\$4) same (time period) with less adj 4 (minute second sec) same rapid	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 11:13
S163	65	wafer with (heat\$3 treat\$4 anneal\$4 pinn\$4) same (time period) with less adj 4 (minute second sec) same rapid adj thermal\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 11:13
S164	0	wafer with (heat\$3 treat\$4 anneal\$4 pinn\$4) same (time period) with less adj 4 (minute second sec) same rapid adj thermal\$4 and pinn\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 11:13
S165	65	wafer with (heat\$3 treat\$4 anneal\$4 pinn\$4) same (time period) with less adj 4 (minute second sec) same rapid adj thermal\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 11:17
S166	0	wafer with (heat\$3 treat\$4 anneal\$4 pinn\$4) same (time period) with less adj 4 (minute second sec) same rapid adj thermal\$4 same ("300" "400" "500")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 11:17
S167	5	wafer with (heat\$3 treat\$4 anneal\$4 pinn\$4) same (time period) with less adj 4 (minute second sec) same rapid adj thermal\$4 and ((degree "c") with ("300" "400" "500"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 11:18

S168	9	S126 and (lamp laser light) with (anneal\$4 heat\$3 treat\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 11:29
S169	26	S126 and field with (heat\$4 treat\$4 anneal\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 11:39
S170	20	S126 and field with (heat\$4 treat\$4 anneal\$4) with after	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 11:42
S171	5	S126 and align\$4 with pinn\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 11:43
S172	1	"20040040628" and align\$4 with pinn\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 11:43
S173	0	S138 and spot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 12:33
S174	5	wafer same spot near2 anneal\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 12:48

S175	317	wafer same spot near2 spot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 12:48
S176	3	wafer same anneal\$4 with spot near2 spot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 12:49
S177	3	wafer and anneal\$4 with spot near2 spot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 12:49
S178	5	wafer and anneal\$4 same spot near2 spot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 12:49
S179	84	wafer and anneal\$4 same point near2 point	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 12:50
S180	28	wafer same anneal\$4 with point near2 point	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 12:50
S181	0	wafer same anneal\$4 with point near2 point same spot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 12:51

S182	111	wafer same anneal\$4 near3 point near2 point	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 12:51
S183	111	wafer same anneal\$4 near3 point near point	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 12:52
S184	12	wafer same laser same anneal\$4 near3 point near point	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 12:52
S185	12	wafer same laser same anneal\$4 near3 point near2 point	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 12:52
S186	12	wafer same laser same anneal\$4 adj3 point near2 point	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 12:53
S187	0	wafer same laser near3 anneal\$4 with point near2 point	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 12:53
S188	0	wafer same laser near3 anneal\$4 same point near2 point	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 12:53

S189	6	laser near3 anneal\$4 same point near2 point	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 12:54
S190	0	laser same pinn\$4 same point near2 point	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 12:54
S191	1	laser same pinn\$4 same spot near2 spot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 12:55
S192	0	laser same pinn\$4 same (spot point) near anneal\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 12:56
S193	118	laser same (spot point) near anneal\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 12:56
S194	10	laser same (spot point) near anneal\$4 same wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 12:56
S195	23	S126 and (liquid helium nitrogen argon vacuum)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/11 13:00
S196	2	((("6123781") or ("4863877"))).PN.	USPAT; USOCR	OR	OFF	2008/01/20 11:19

S197	2	"20040040628"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/20 11:19
S198	4	S196 S197	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 09:52
S199	2	((("6123781") or ("4863877"))).PN.	USPAT; USOCR	OR	OFF	2008/01/22 09:52
S200	2	"20040040628"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 09:52
S201	4	S199 S200	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 09:52
S202	4	S201	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 11:04
S203	4	S202 and anneal\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 10:05
S204	3	S202 and (magnet\$7 field)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 10:17

S205	21	((magnet\$7 field) with anneal\$5 with wafer).dlm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 10:10
S206	3	((magnet\$7 field) with anneal\$5 with wafer and (flash lamp laser flash\$5 rta) with anneal\$5).dlm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 10:30
S207	1	S202 and S206	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 10:13
S208	4	("5496759" "6027948" "6048739").PN. OR ("6918965").UPFN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/01/22 10:16
S209	3	S208 and (magnet\$7 field) and anneal\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 10:21
S210	1	S208 and (magnet\$7 field) same pin\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 10:21
S211	2	S208 and (magnet\$7 field) same (pin\$4 fix\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 10:21
S212	3	S206 and (pin\$5 fix\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 10:29

S213	0	S212 and (pin\$5 fix\$5) with (flash lamp laser flash\$5 rta)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 10:33
S214	3	S212 and (pin\$5 fix\$5) with anneal\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 10:35
S215	3	S212 and (pin\$5 fix\$5) with anneal\$5 and heat\$4 with anneal\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 10:53
S216	2974	148/108.ccls. 438/3.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 10:53
S217	2	"20040040628"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 10:57
S218	1	S217 and local\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 11:00
S219	1	S217 and local\$4 and (anneal\$4 near\$5 layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 11:00

S220	0	S217 and degree	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 11:01
S221	1	S217 and anneal\$4 with c	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 11:01
S222	0	S217 and ("300" "400" "500")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 11:01
S223	40	tuttle.in. and anneal\$4 and wafer and magnet\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 11:05
S224	39	tuttle.in. and anneal\$4 and wafer and magnet\$5 and (pin \$5 fix\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 11:05
S225	4	tuttle.in. and anneal\$5 and wafer and magnet\$5 and ((pin \$5 fix\$5) with (magnet\$5 anneal\$5))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 11:20
S226	4	S225 and laser	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 11:21

S227	4	S225 and local\$5 with (magnet\$5 field)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 11:24
S228	5	"20040040628" "20050133118"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 11:24
S229	3	S228 and local\$5 with (magnet\$5 field)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 11:24
S230	0	S228 and local\$5 with (magnet\$5 field) with (pin\$5 fix\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 11:25
S231	3	S228 and local\$5 with (magnet\$5 field) same (pin\$5 fix \$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 11:26
S232	3	S228 and local\$5 with (magnet\$5 field) same (pin\$5 fix\$5 align\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 11:36
S233	1	annea\$4 with (spot adj spot)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 11:36

S234	27	anneal\$4 with (line adj line)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 11:40
S235	28	S233 S234	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 11:38
S236	8	S235 and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 11:37
S237	20	S235 not S236	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 11:38
S238	302	wafer with ((line adj line) (spot adj spot))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 11:40
S239	28	wafer with ((line adj line) (spot adj spot)) same laser	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 11:41
S240	1	wafer with ((line adj line) (spot adj spot)) same laser with (heat\$4 treat\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 11:54

S241	2	"20050087519"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 11:54
S242	1	S241 and magnet\$5 with less	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 11:56
S243	2	S241 and magnet\$5 with entir\$7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 11:57
S244	5	S228 and magnet\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 12:46
S245	3373	(Helmholtz coil) with magnet\$7 same wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 11:58
S246	51	Helmholtz with magnet\$7 same wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 11:59
S247	5	Helmholtz with magnet\$7 same wafer same (pin\$4 fix\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 12:07

S248	193	anneal\$5 with (magnet\$7 pin\$5) with ("300" "400" "500" "350" "450") with c	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 12:08
S249	216	anneal\$5 with (magnet\$7 pin\$5) with ("300" "400" "500" "350" "450") with (c celcius centigrade)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 12:11
S250	8	S249 same wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 12:10
S251	8	S249 and anneal\$5 with wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 12:49
S252	217	anneal\$5 with (magnet\$7 pin\$5) with ("300" "325" "375" "425" "475" "400" "500" "350" "450") with (c celcius centigrade)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 12:11
S253	218	anneal\$5 with (magnet\$7 pin\$5) with ("275" "525" "300" "325" "375" "425" "475" "400" "500" "350" "450") with (c celcius centigrade)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 12:32
S254	66	S253 and magnet\$5 with layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 12:12

S255	11	S253 and magnet\$5 with layer same wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 12:17
S256	5	S253 and magnet\$5 with layer same wafer and sec\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 12:18
S257	30	anneal\$5 with magnet\$5 with layer same wafer same sec\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 12:20
S258	0	anneal\$5 with magnet\$5 with layer same wafer same ("1" "60") near3 sec\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 12:19
S259	17	anneal\$5 with magnet\$5 with layer same wafer same min\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 12:21
S260	15	S253 and cool\$4 with (liquid helium nitrogen argon vacuum)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 12:32
S261	1	S253 and cool\$4 with (liquid helium nitrogen argon vacuum) same wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 12:30

S262	175	anneal\$5 with wafer with ("275" "525" "300" "325" "375" "425" "475" "400" "500" "350" "450") with (c celcius centigrade)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 12:35
S263	12	S262 and cool\$4 with (liquid helium nitrogen argon vacuum) same wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 12:33
S264	172	anneal\$5 with wafer same cool\$4 with (liquid helium nitrogen argon vacuum)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 12:36
S265	17	anneal\$5 near2 wafer same cool\$4 near2 (liquid helium nitrogen argon vacuum)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 12:36
S266	5	S228 and cool\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 12:46
S267	0	laser with anneal\$5 with wafer same cool\$4 with (helium nitrogen argon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 12:50
S268	0	laser with anneal\$5 with wafer same cool\$4 with (vacuum liquid)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 12:50

S269	3	laser with anneal\$5 with wafer and wafer with cool\$4 with (vacuum liquid helium nitrogen argon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/22 13:17
S270	1	("5763108").PNL	USPAT; USOCR	OR	OFF	2008/01/22 13:17
S271	2	"20050233512"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/11 12:28

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